

Comparative Evaluation of Advanced 3-level Inverter/Converter Topologies against 2-level Systems

M. Schweizer, T. Friedli and J.W. Kolar

ETH Zurich

Power Electronic Systems Laboratory

schweizer@lem.ee.ethz.ch

www.pes.ee.ethz.ch



Outline

- Introduction
- 3-level T-type converter topology
- 3-level NPC topology with SiC diodes
- Modulation and DC-link balancing
- Comparison of passives
- Comparison of semiconductor chip area
- Optimization potential
- Summary

Introduction to the topic

■ 3-phase 3-level topologies for low voltage applications - a **bad idea**?

Contra

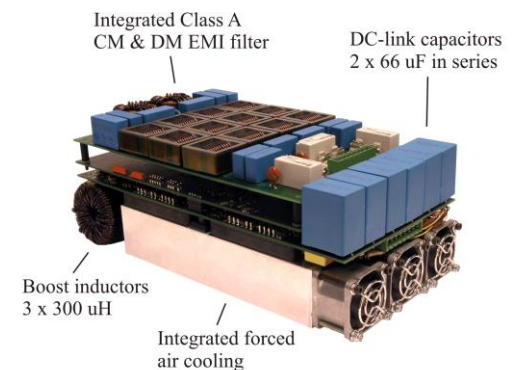
- *More semiconductors*
- *More gate drive units*
- *Increased complexity*
- *DC-link balancing*
- *Increased costs!*

Pro

- *High efficiency at increased switching frequency*
- *Smaller passives*

■ But is this the full story?

- *Alternative, suitable 3-level concepts*
- *Enhancements with SiC diodes*
- *Necessary semiconductor chip area*
- *Optimization for operating point*
- *AC-AC converter DC-link balancing*



Considered voltage source converter topologies

■ 2-level VSC

- *Simple, low part count, robust, cheap*
- *Reduction of switching losses with SiC diodes*

■ 3-level T-type

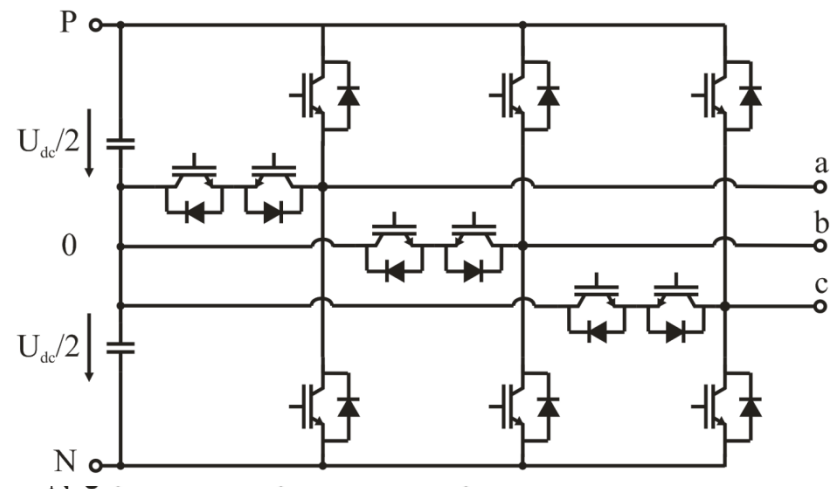
- *3 bidirectional switches to middle voltage*

■ 3-level NPC

- *Enhancement with SiC diodes?*

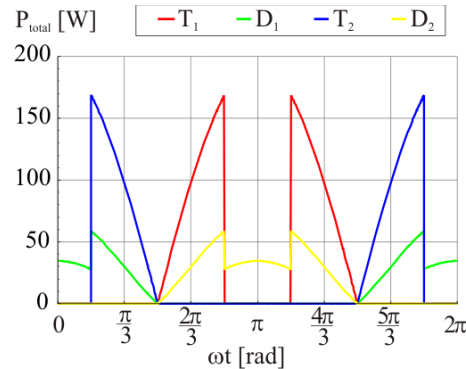
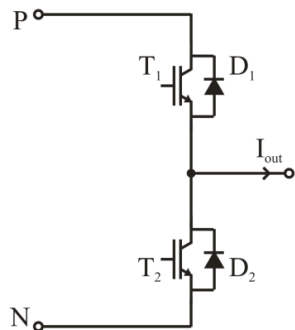
■ AC-AC converters

- *Advantages for DC-link balancing*



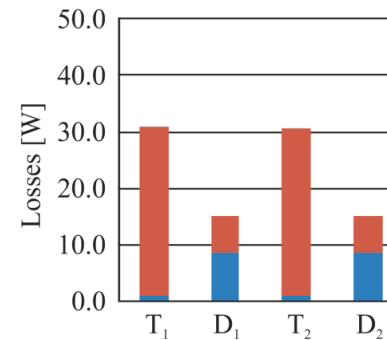
2-level voltage source converter

1200V IGBT: Infineon IKW25T120

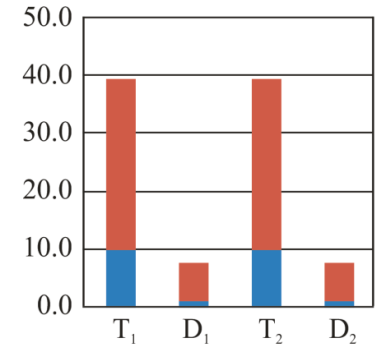


$P_n = 10\text{kW}$, $U_{dc} = 700\text{V}$, $\hat{U}_n = 325\text{V}$, $\hat{I}_n = 20.5\text{A}$, $\varphi = 0/180^\circ$

Rectifier operation

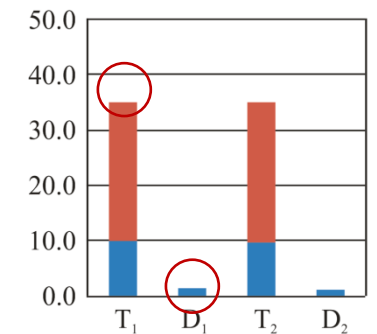
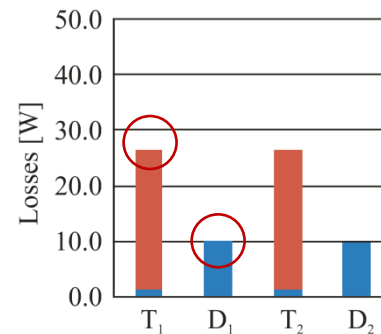


Inverter operation



■ Conduction losses ■ Switching losses (32 kHz)

- High switching losses
- Mean loss distribution is similar for rectifier and inverter operation
- Clear benefit from SiC diodes

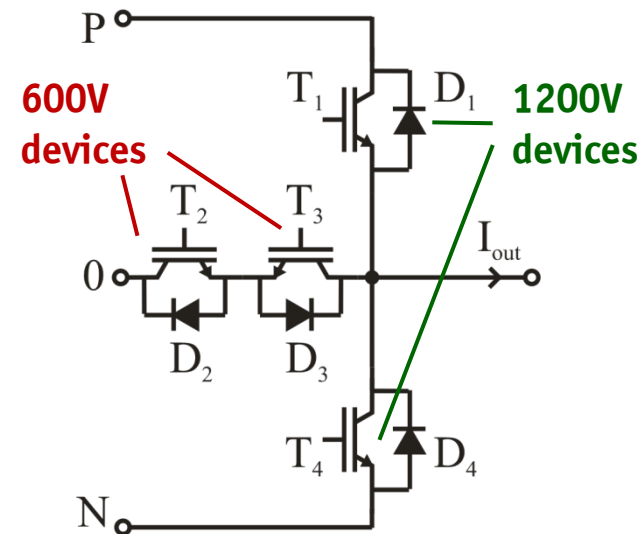


loss reduction: -25%

IKW25T120 + Cree C2D10120 scaled to 25A

3-level T-type – An alternative VSC topology

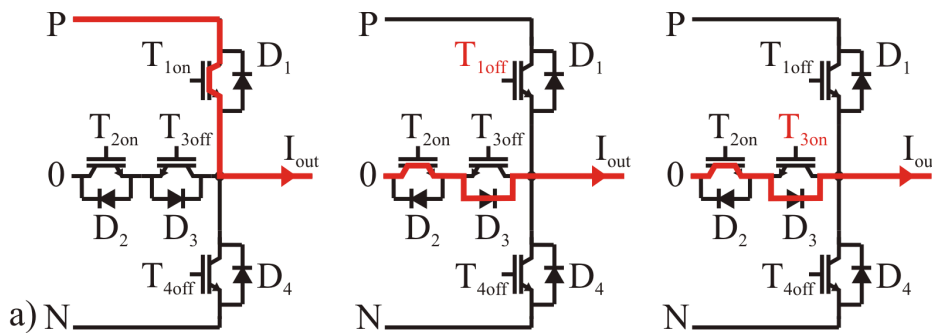
- Simple extension of the conventional 2-level topology to a 3-level topology?
- Bidirectional middle switch with two IGBTs in common emitter connection
- Combination of **1200V** and **600V** devices
 - *600V IGBT: low switching losses, low forward voltage drop*
 - *Only one more isolated gate drive supply per phase leg (compared to 2-level)*



T-type topology - commutation

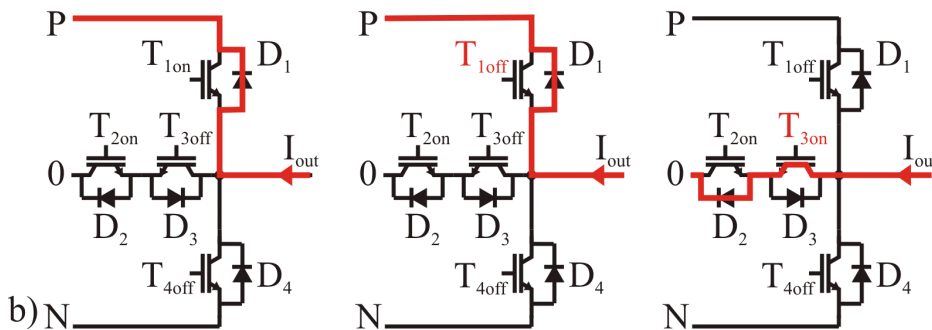
	T_1	T_2	T_3	T_4
P	1	1	0	0
0	0	1	1	0
N	0	0	1	1

Current independent commutation sequence



Transition $P \rightarrow 0$, $I_{out} > 0$

- 1) T_1 & T_2 closed, T_3 & T_4 open
- 2) T_1 opens $\rightarrow I_{out}$ comm. to 0 over D_3 & T_2
- 3) T_3 closes after turn-on delay T_d



Transition $P \rightarrow 0$, $I_{out} < 0$

- 1) T_1 & T_2 closed, T_3 & T_4 open
- 2) T_1 opens
- 3) T_3 closes after turn-on delay T_d
 I_{out} comm. to 0 over T_3 & D_2

T-type topology – loss calculation

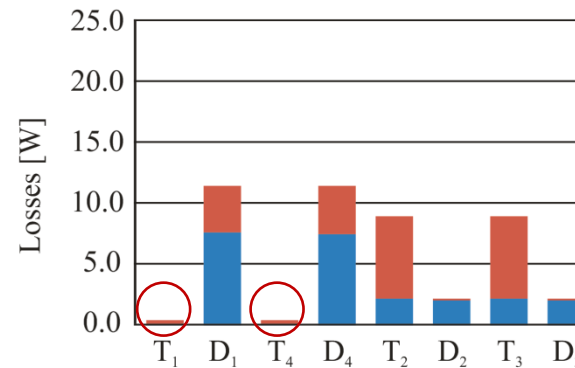
- Switching losses change because of mixed IGBT types
- Loss energy measured with T-type bridge leg test setup
- Reduced switching losses
 - Commutation voltage is only $U_{dc}/2$
- Distinct loss distribution profile depending on operating point

1200V IGBT: Infineon IKW25T120
600V IGBT: Infineon IKW30N60T

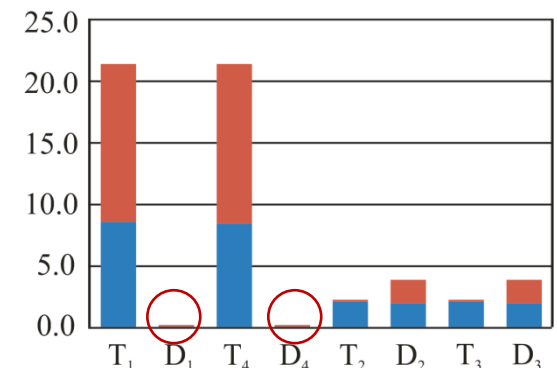
Element	Energy	Datasheet difference
1200V IGBT turn on	0.81 mJ	-19%
1200V IGBT turn off	1.27 mJ	-5%
1200V Diode turn off	0.64 mJ	+22%
600V IGBT turn on	0.68 mJ	+90%
600V IGBT turn off	0.42 mJ	+9%
600V Diode turn off	0.31 mJ	+85%

@ 300V, 20A, 125°C

Rectifier operation



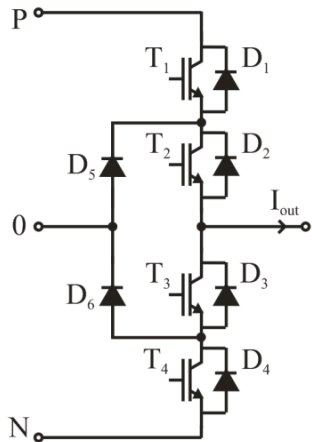
Inverter operation



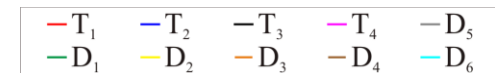
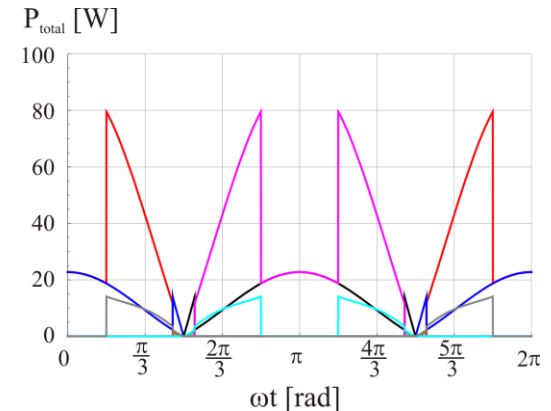
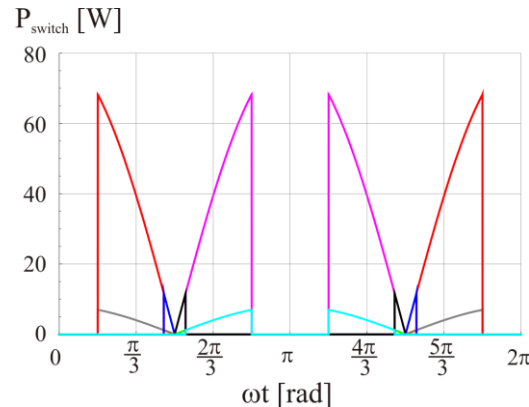
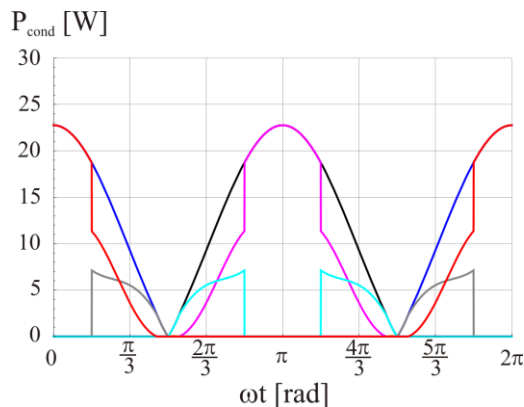
$P_n = 10\text{kW}$, $\hat{U}_n = 325\text{V}$, $\hat{I}_n = 20.5\text{A}$, $\varphi = 0/180^\circ$

■ Conduction losses ■ Switching losses (32 kHz)

The 3-level NPC converter

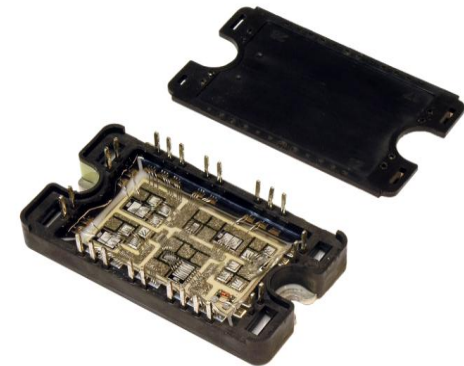
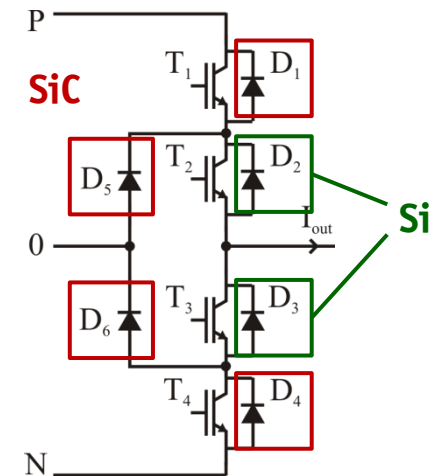


- **600V devices: Low switching losses, low forward voltage drop**
- **Optimal clamping possible**
 - *Reduction of switching losses*
 - *DC-link balancing is restricted*
- **Can we improve the 3-level NPC converter?**
 - *SiC diodes*
 - *Semiconductor chip area optimization*



The 3-level NPC converter with SiC diodes

- Should we replace all diodes with SiC?
 - *Very expensive!*
 - *Increased conduction losses*
- 3-level NPC Modulation
 - *Analysis of occurring loss energies*
 - *Direct transition $P \rightarrow N$ or $N \rightarrow P$ is omitted*
 - *D_2 and D_3 never show reverse recovery effect!*
 - *Leave it in conventional Si!*
- Consider characteristic loss distribution
 - *Inverter operation (solar inverter)*
 - *Replace only D_5 and D_6 with SiC diodes*
 - *Rectifier operation (pfc grid interface)*
 - *Replace only D_1 and D_4 with SiC diodes*



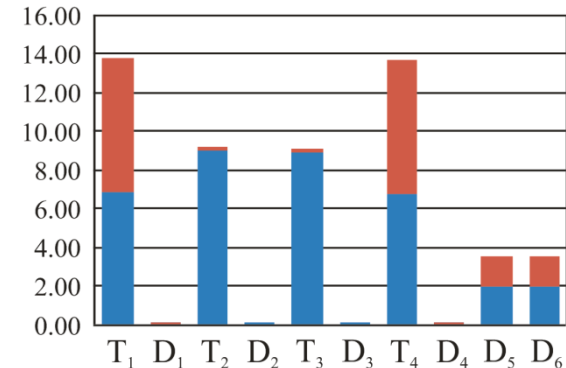
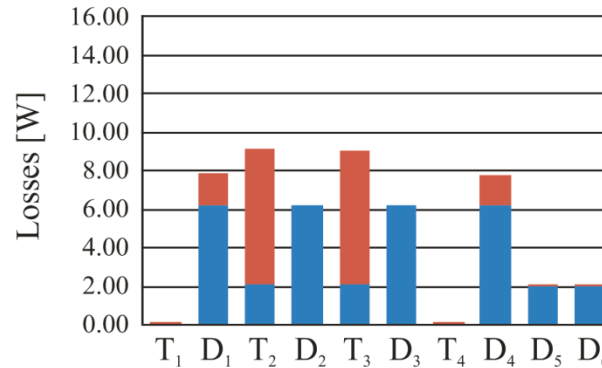
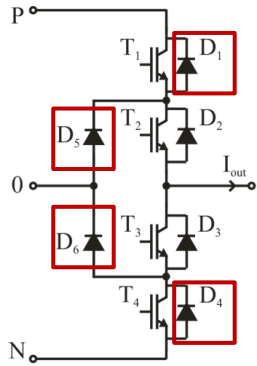
Custom SiC 3-level NPC bridge
leg module

Average Device Losses

600V IGBT: Infineon IKW30N60T

Rectifier operation

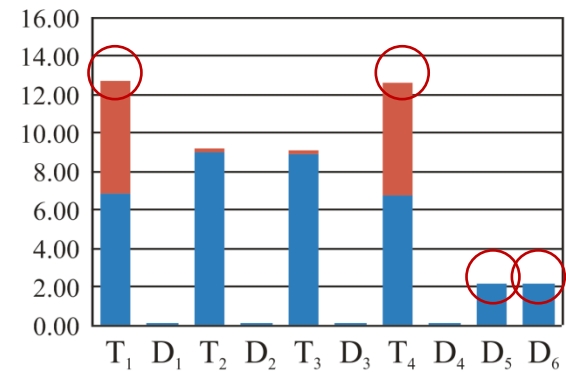
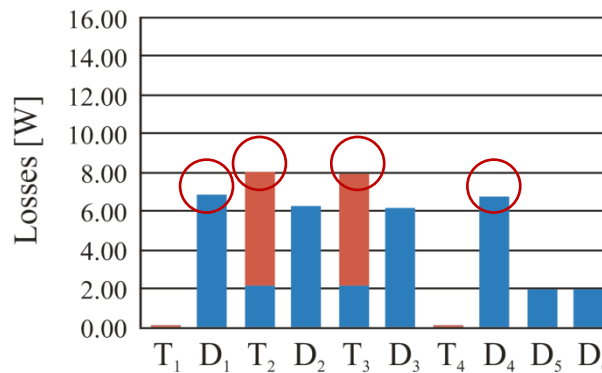
Inverter operation



$P_n = 10\text{kW}$, $U_{dc} = 700\text{V}$, $\hat{U}_n = 325\text{V}$, $\hat{I}_n = 20.5\text{A}$, $\varphi = 0/180^\circ$

■ Conduction losses ■ Switching losses (48 kHz)

- Replace D_1 and D_4 with SiC
- Replace D_5 and D_6 with SiC

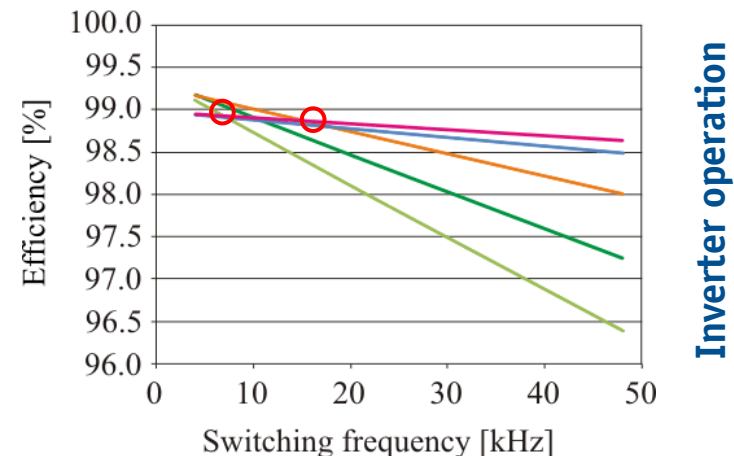
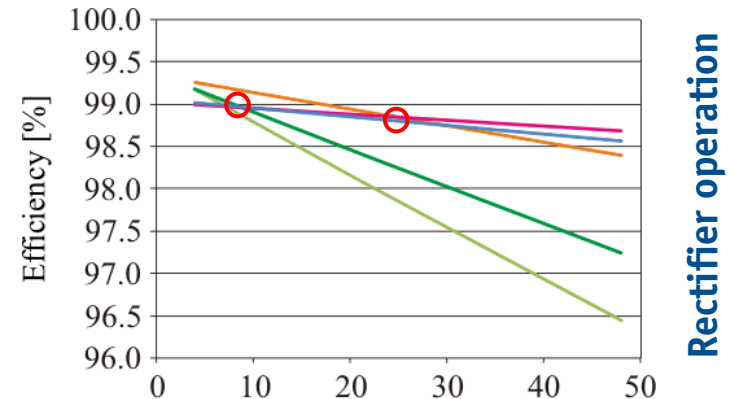


IKW30N60T + Cree CSD10060 scaled to 30A

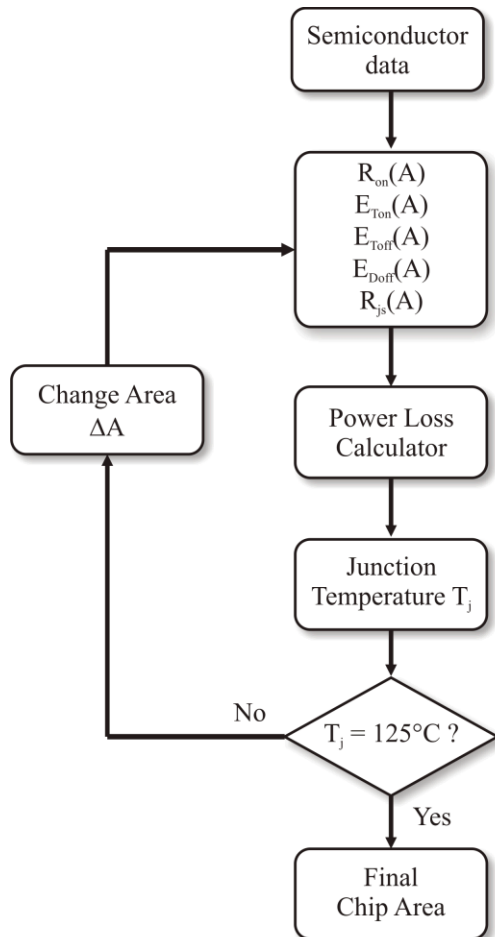
Simple Efficiency Comparison

$$P_n = 10\text{kW}, U_{dc}=700\text{V}, \hat{U}_n=325\text{V}, \hat{I}_n=20.5\text{A}, \varphi=0/180^\circ$$

- 2-level is efficient for low switching frequency
- SiC diodes can extend f_s range
- T-type topology is very efficient for medium f_s (8 – 20 kHz)
- 3-level NPC efficiency has flattest dependency on f_s
- Suitable for high f_s
- SiC diodes make only sense for very high f_s (>50 kHz)



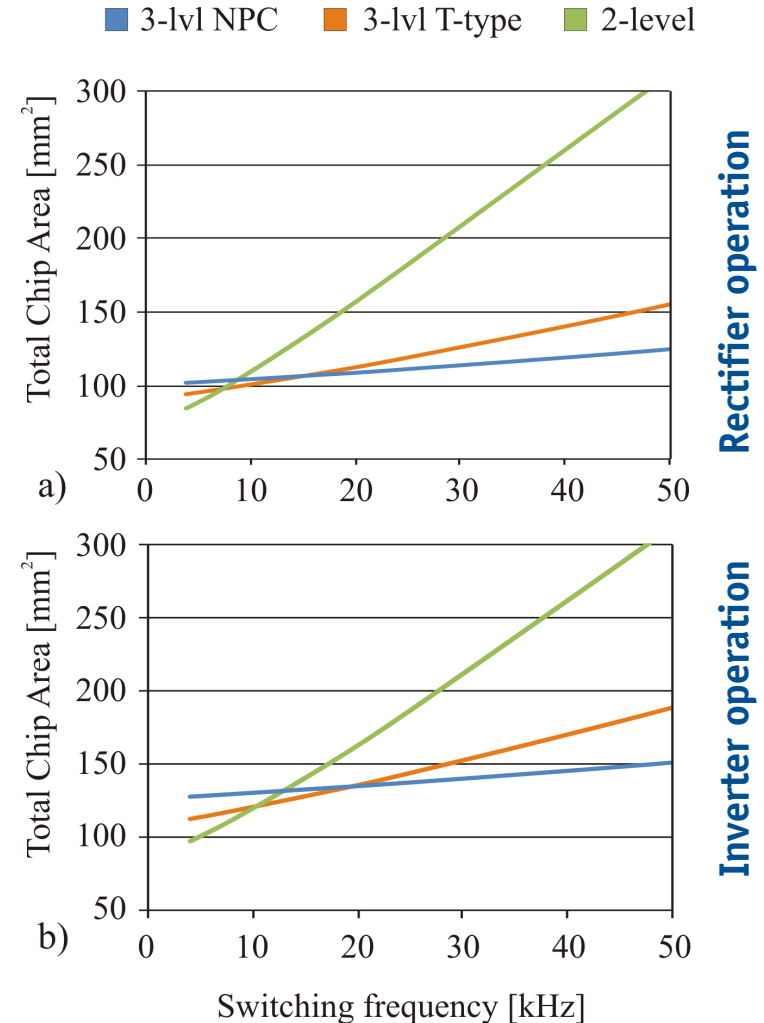
Comparison of semiconductor chip area



- Non-uniform distribution of losses over the semiconductor chips
- Low losses in a device
 - *Make chip smaller*
- High losses in a device
 - *Make chip bigger*
- Reach $T_j = 125^\circ\text{C}$ in each chip
- **Idea: Operating point dependent chip size optimization**
 - *Fair topology comparison*
 - *Reduce module costs*
- Cheap mass market modules:
 - *Pure inverter/rectifier 3-level modules for fixed operating point (solar inverter/pfc)*

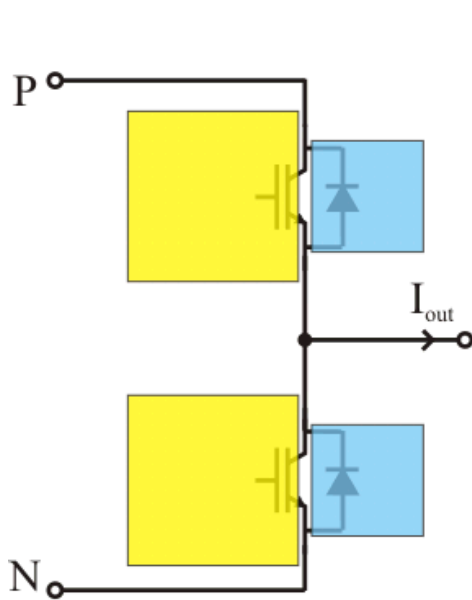
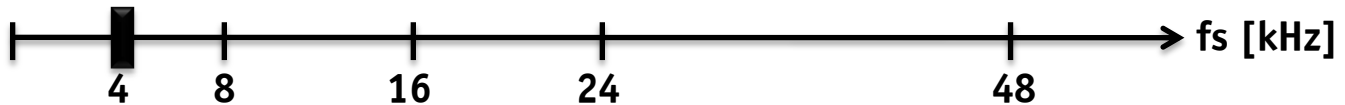
Optimization results for $T_j = 125^\circ \text{ C}$

- **2-level topology**
 - Losses are **concentrated** in few chips
 - Chip size increases sharply with frequency
 - Total chip area of 2-level is smallest only for low switching freq. ($f_s < 10 \text{ kHz}$)!
- **3-level topologies**
 - Losses are **distributed** over many semiconductors
 - Chip size reduction possible
 - Losses increase only slightly with f_s
 - Distinct loss profile (Operating point)
- **Total semiconductor area:**
 - For $f_s = 35 \text{ kHz}$: $A_{2\text{-level}} \approx 2 \cdot A_{3\text{-lvl NPC}}$!

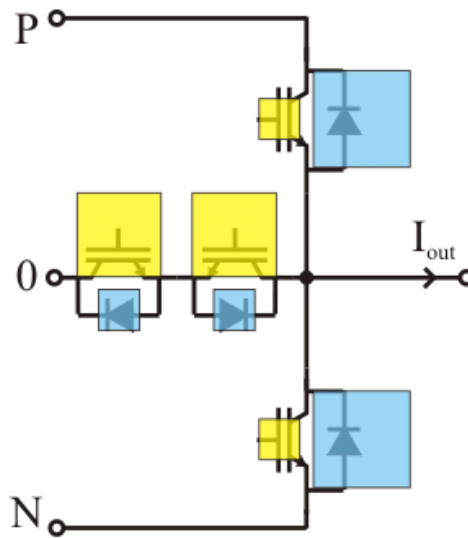


Necessary chip area for $T_j=125^\circ\text{C}$ (rectifier operation)

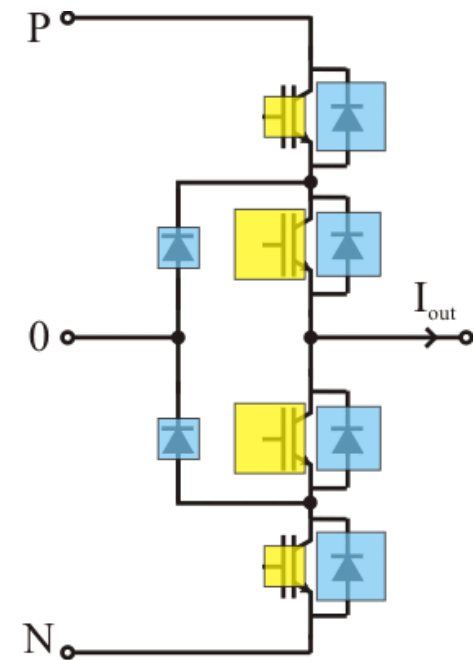
Switching frequency



302.3 (+255%)



152.0 (+61%)

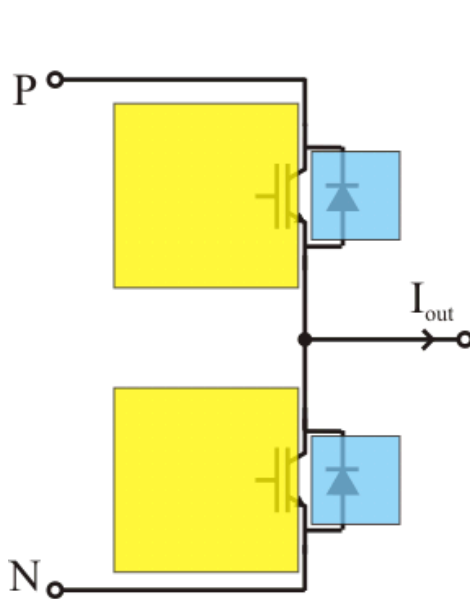
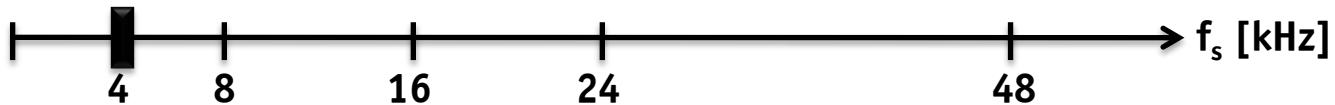


123.5 (+21%)

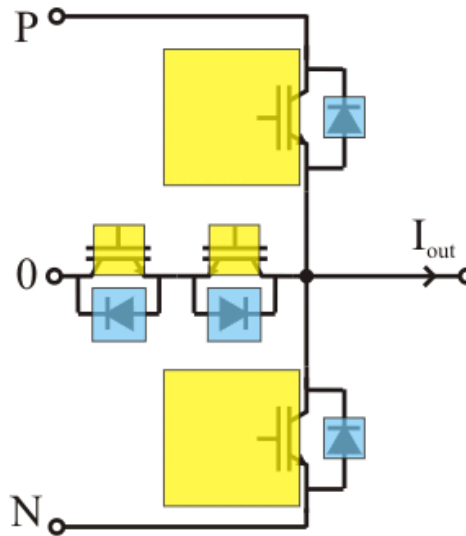
Total area [mm²] (3 phases)

Necessary chip area for $T_j=125^\circ\text{C}$ (inverter operation)

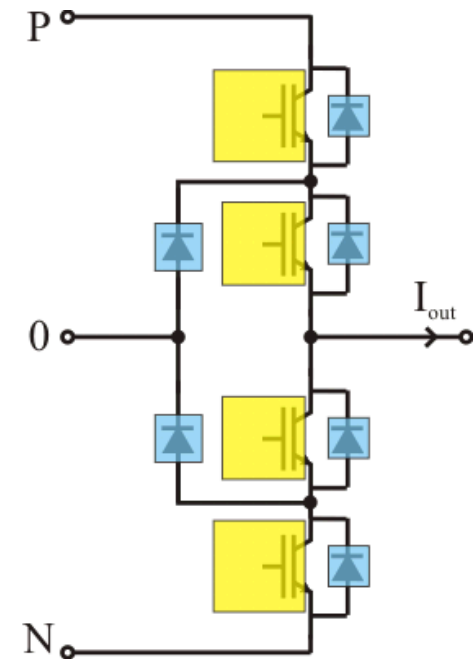
Switching frequency



303.4 (+209%)



185.2 (+64%)

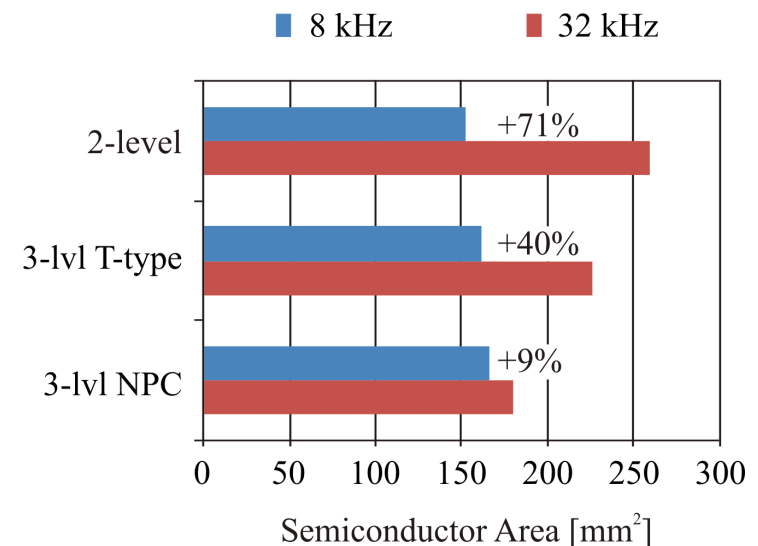


150.6 (+17%)

Total area [mm^2] (3 phases)

Total semiconductor area for mixed mode operation ($T_j=125^\circ\text{C}$)

- General purpose module (mixed mode)
 - *Take maximum chip die sizes from rectifier and inverter operation*
 - *Only a first approximation, more operating points have to be considered*
- Increase of switching frequency over audible range (8 $\rightarrow$ 32 kHz)
 - *Total semiconductor chip area increases by 70% for 2-level converter*
 - *Whereas the 3-lvl NPC total chip area increases only by 10%*



Passives – Boost inductor

- Boost inductor design for a max. current ripple of 20% $\hat{I}_n$

- 2-level:

$$L_{2lvl} = \frac{1}{f_s} \cdot d_{1,2lvl} \cdot \frac{2/3 U_{dc} - \hat{U}_n}{\Delta i_{pp}}$$

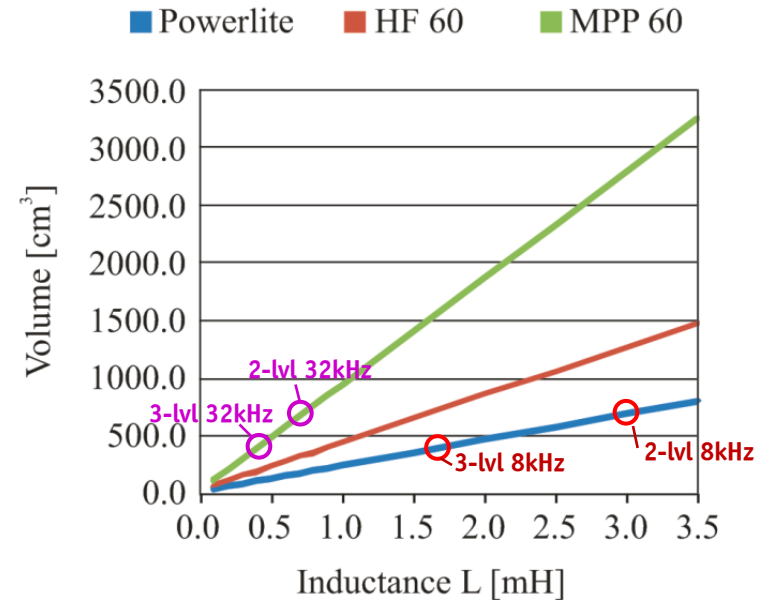
- 3-level:

$$L_{3lvl} = \frac{1}{f_s} \cdot d_{1,3lvl} \cdot \frac{2/3 U_{dc} - \hat{U}_n}{\Delta i_{pp}}$$

- Ratio of inductances:

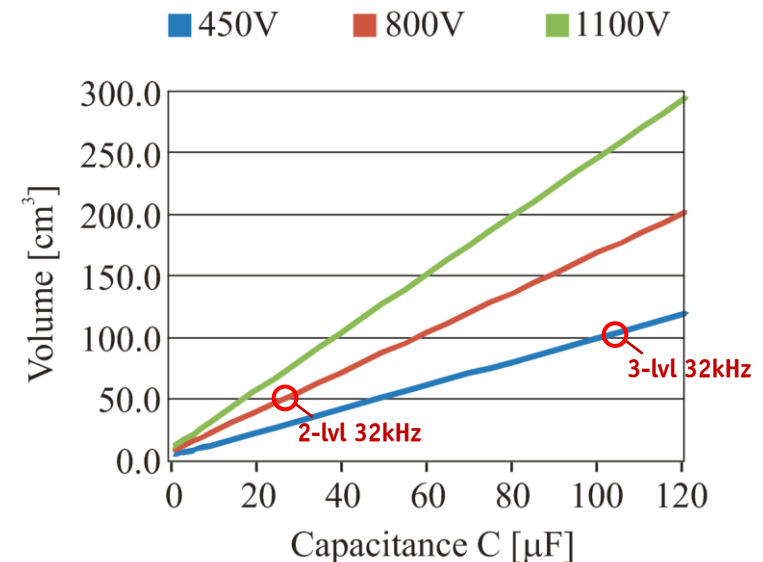
$$\frac{L_{3lvl}}{L_{2lvl}} = \frac{d_{1,3lvl}}{d_{1,2lvl}} = 55\%$$

- Volume of boost inductor can be reduced if same core material is used



Passives – DC-link capacitor

- DC-link capacitor can be designed for different aspects
 - *Energy related (control, plant)*
 - *Minimizing capacitor*
 - *Balancing (3-level)*
- 2-level:
 - $C_{dc,2lvl}$
- 3-level:
 - *Two times $2 \cdot C_{dc}$ in series: Sum of $4 \cdot C_{dc}$*
 - *Half voltage rating*
- **Total volume increases but is still small compared to the boost inductor volume**



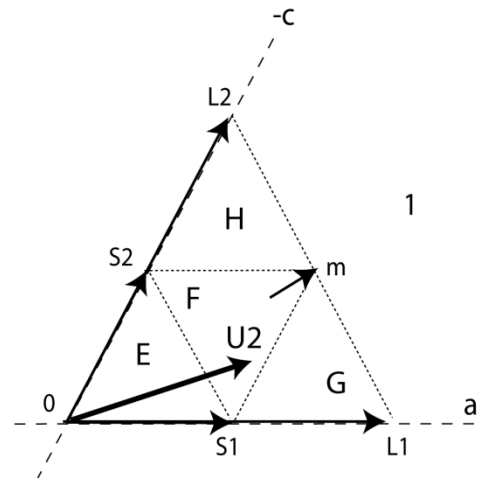
3-level topology – Modulation

- Space vector modulation for 3-level topology is “simple”:

- Main sector detection
 - Rotation of system to reference sector 1
 - Detection of subsector (rotations)
 - Calculation of Vector on-times

- Space vector modulation [1]

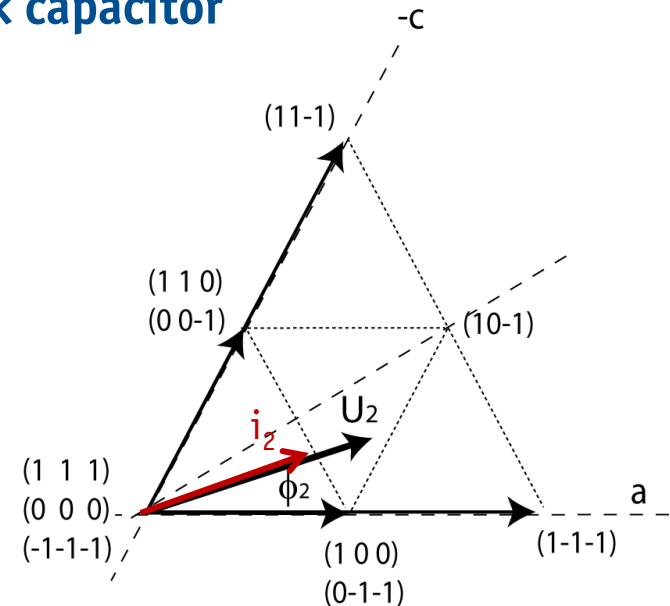
E	$T_{s1} = \alpha \times 2 \times T_c \times \sin(60^\circ - \theta)$
	$T_{s2} = \alpha \times 2 \times T_c \times \sin \theta$
	$T_0 = T_c - T_{s1} - T_{s2}$
F	$T_{s1} = T_c - \alpha \times 2 \times T_c \times \sin \theta$
	$T_{s2} = T_c - \alpha \times 2 \times T_c \times \sin(60^\circ - \theta)$
	$T_m = \alpha \times 2 \times T_c \times \sin(60^\circ + \theta) - T_c$
G	$T_{s1} = 2T_c - \alpha \times 2 \times T_c \times \sin(60^\circ + \theta)$
	$T_{L1} = \alpha \times 2 \times T_c \times \sin(60^\circ - \theta) - T_c$
	$T_m = \alpha \times 2 \times T_c \times \sin \theta$
H	$T_{s2} = 2T_c - \alpha \times 2 \times T_c \times \sin(60^\circ + \theta)$
	$T_{L2} = \alpha \times 2 \times T_c \times \sin \theta - T_c$
	$T_m = \alpha \times 2 \times T_c \times \sin \theta (60^\circ - \theta)$



Space vector U_2 is always modulated with the 3 closest discrete space vectors

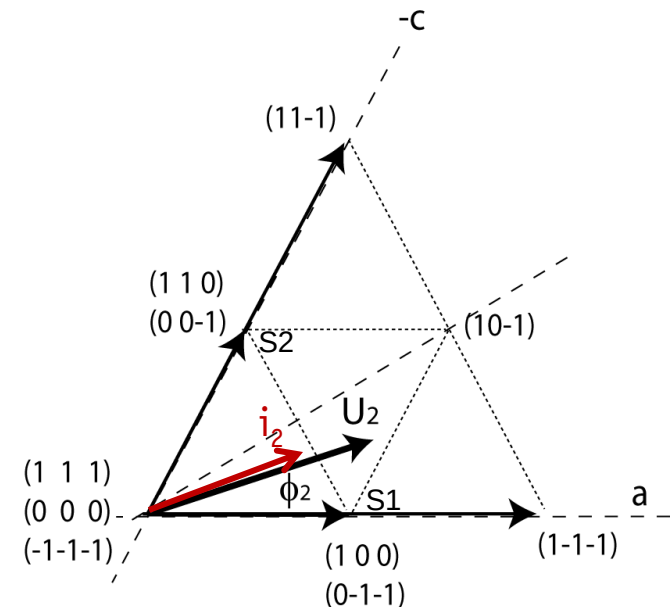
3-level voltage source rectifier – Optimal Clamping

- Optimal clamping is possible
 - *Highest phase current is not switched*
 - *Switching losses get reduced by $\approx 30\%$*
- Vector Sequence defines clamping scheme
- Periodically loads top and bottom dc-link capacitor
 - $0 < f_2 < 30^\circ$:
 - Phase A clamped to positive DC-link rail
 - i_A not switched at maximum amplitude $(1\ 1\ 0)\ (1\ 0\ 0)\ (1\ 0\text{-}1)\ (1\ 0\ 0)\ (1\ 1\ 0)$
 - $30^\circ < f_2 < 60^\circ$:
 - Phase C clamped to negative DC-link rail
 - i_c not switched at maximum amplitude $(0\text{-}1\text{-}1)\ (0\ 0\text{-}1)\ (1\ 0\text{-}1)\ (0\ 0\text{-}1)\ (0\text{-}1\text{-}1)$



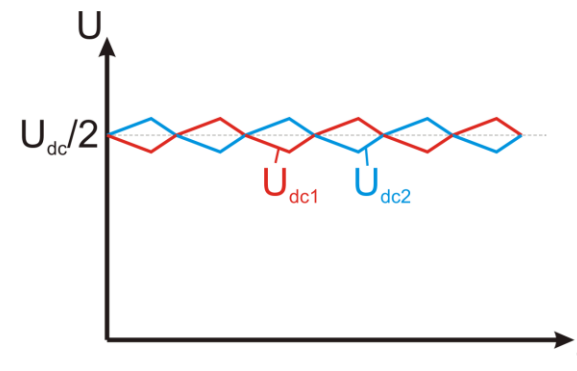
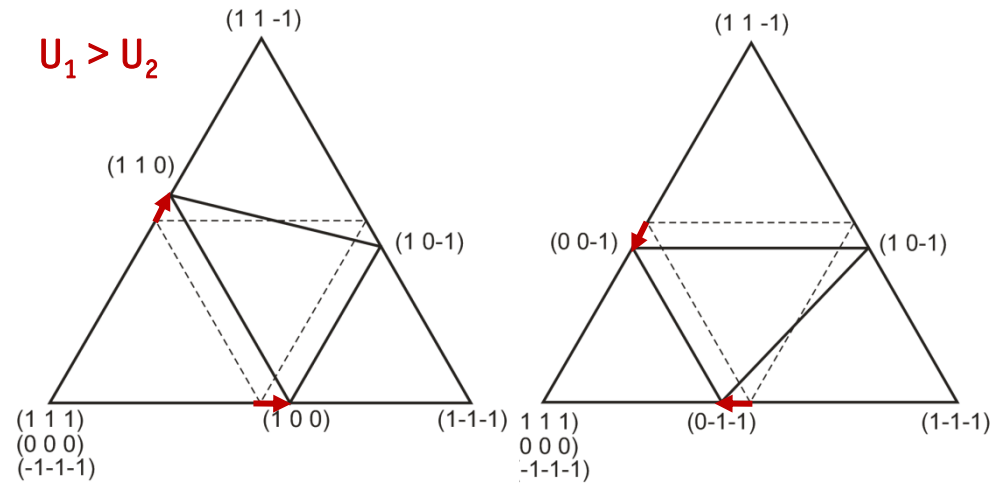
3-level voltage source rectifier - Balancing

- The DC-link capacitors may be loaded unbalanced
- Small vectors **S1** and **S2**:
 - *Redundant vectors invert current flowing into capacitor mid-point*
 - *Alternative switching sequences exist:*
Charge C1: (1 1 0) (1 0 0) (1 0-1) (1 0 0) (1 1 0)
Charge C2: (0-1-1) (0 0-1) (1 0-1) (0 0-1) (0-1-1)
- Choose appropriate sequence depending on voltage unbalance with hysteresis controller
- Optimal clamping not always possible



Modulation with link unbalance

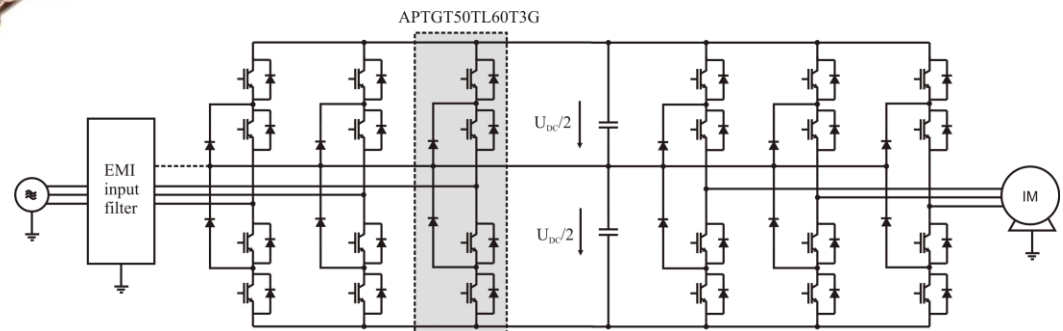
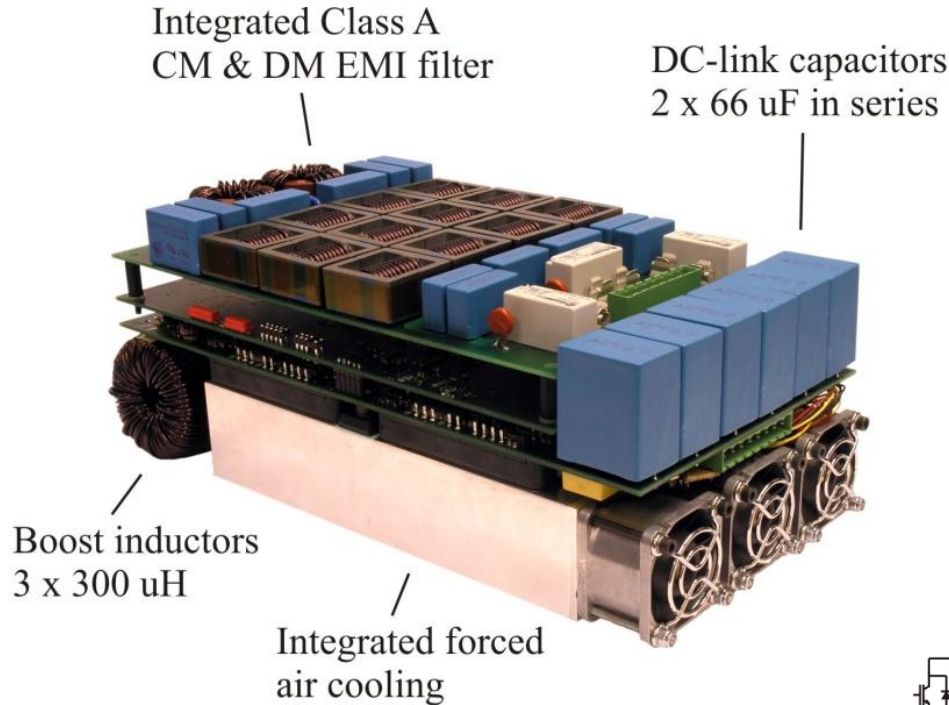
- Active vectors move due to link unbalance
- Sector borders move
- **Redundant middle vectors move in opposite direction**
- Sector detection and on-time calculation can be adapted
- AC-AC converters:
 - Inverter stage
 - *optimal clamping (higher current amplitude)*
 - Rectifier stage
 - *Balancing*



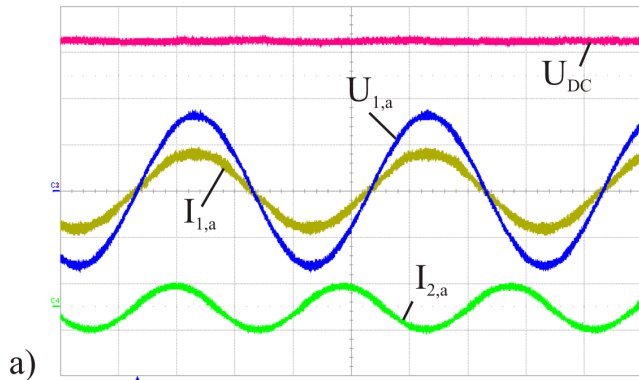
3LVL NPC – AC-AC back-to-back converter prototype

Specifications

- $P_n = 10 \text{ kW}$
- $U_n = 230 \text{ V RMS}$
- $U_{dc} = 700 \text{ V}$
- $f_n = 50 \text{ Hz} \dots 800 \text{ Hz}$
- $f_s = 48 \text{ kHz}$
- Power density: 2.9 kW/l
- Weight: 5 kg
- Efficiency: 96% (SiC 96.5%)
- CISPR Class A (B possible)



3LNPC-VLBBC Prototype 50Hz Operation



a) Operating conditions:

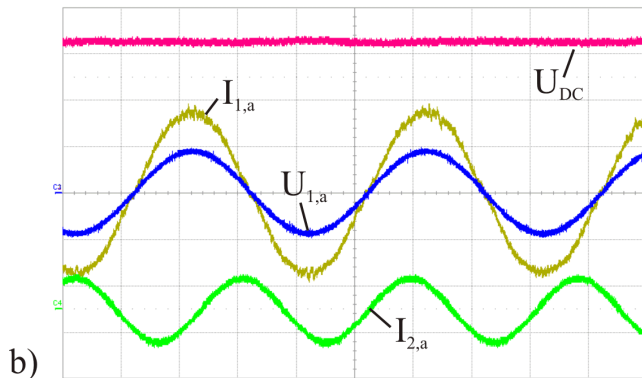
$P_1=4\text{kW}$, $U_1=230\text{V}$, $f_1=50\text{ Hz}$, $f_2=70\text{ Hz}$

THD $I_1 = 3.0\%$

THD $I_2 = 2.2\%$

Scale: $t=5\text{ms/div}$, $I_1=10\text{A/div}$,

$I_2=24\text{A/div}$, $U_1=200\text{V/div}$, $U_{dc}=200\text{V/div}$



b) Operating conditions:

$P_1=8\text{kW}$, $U_1=230\text{V}$, $f_1=50\text{ Hz}$, $f_2=70\text{ Hz}$

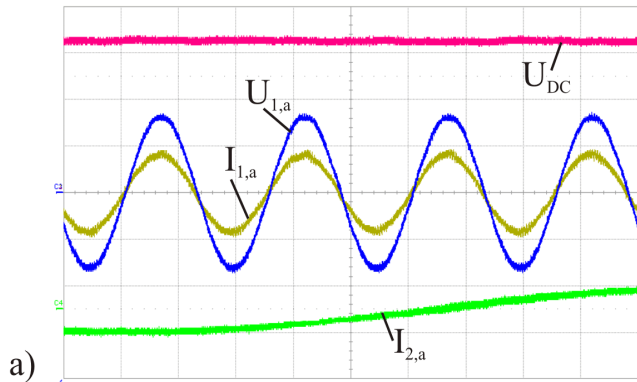
THD $I_1 = 3.5\%$

THD $I_2 = 2.2\%$

Scale: $t=5\text{ms/div}$, $I_1=10\text{A/div}$,

$I_2=24\text{A/div}$, $U_1=350\text{V/div}$, $U_{dc}=200\text{V/div}$

3LNPC-VLBBC Prototype 800Hz Operation



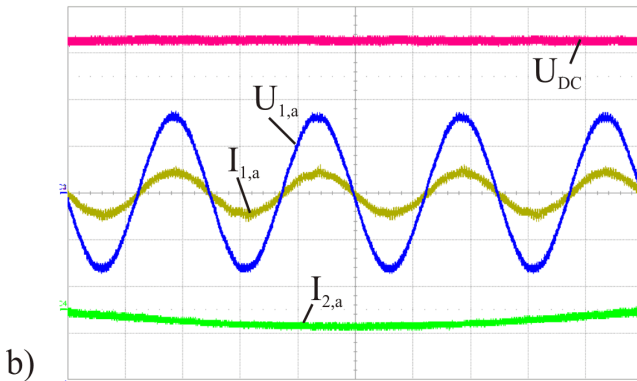
a) Operating conditions:

$P_1=4\text{kW}$, $U_1=230\text{V}$, $f_1=800\text{ Hz}$, $f_2=70\text{ Hz}$

THD $I_1 = 2.9\%$

THD $I_2 = 2.2\%$

Scale: $t=500\mu\text{s}/\text{div}$, $I_1=10\text{A}/\text{div}$,
 $I_2=24\text{A}/\text{div}$, $U_1=200\text{V}/\text{div}$, $U_{dc}=200\text{V}/\text{div}$



b) Operating conditions:

$P_1=2\text{kW}$, $U_1=230\text{V}$, $f_1=800\text{ Hz}$, $f_2=70\text{ Hz}$

Capacitive input filter current is fully compensated even at low power. Unity power factor is achieved.

Summary

- 3-phase 3-level converters could be used for low voltage applications with high switching frequency
- Desirable properties:
 - *High f_s possible → high dynamics, no audible noise, slightly reduced passives (weight, costs)*
 - *High efficiency*
 - *Loss distribution over many chips*
 - *Only small chip area necessary → costs could be reduced*
 - *Only small part count increase (3-level T-type)*
 - *High optimization potential for pure inverter / rectifier modules*
- Remaining drawbacks:
 - *Increased complexity*
 - *Increased part count (3-level NPC)*

Literature

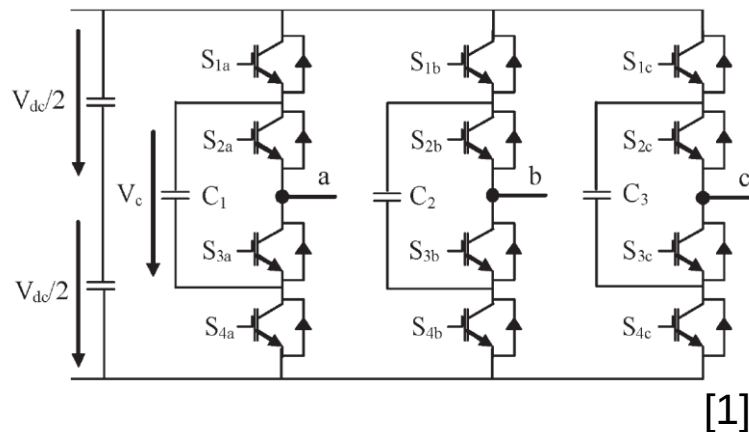
- M. Schweizer, T. Friedli, and J.W. Kolar, "Comparison and implementation of a 3-level NPC voltage link back-to-back converter with SiC and Si diodes", in Proc. of 25th annual IEEE Applied Power Electronics Conf. and Exposition APEC 2010, pp. 1527-1530, 2010.
- M. Schweizer, I. Lizama, T. Friedli, and J.W. Kolar, "Comparison of the chip area usage of 2-level and 3-level voltage source converter topologies", in Proc. of 36th annual Conf. of IEEE Industrial Electronics, IECON 2010, to be published.
- T. Friedli and J.W. Kolar, "A semiconductor area based assessment of AC motor drive converter topologies", in Proc. of 24th Annual IEEE Applied Power Electronics Conf. and Exposition APEC 2009, pp. 336-342.
- R. Teichmann and S. Bernet, "A comparison of three-level converters versus two-level converters for low-voltage drives, traction and utility applications", IEEE Trans. Ind. Appl., vol. 41, pp. 855-865, May-June 2005.
- B. Kaku, I. Miyashita, and S. Sone, "Switching loss minimised space vector PWM method for IGBT three-level inverter", IEE Proc. of Electric Power Applications, vol. 144, pp. 182-190, May 1997.
- J. Pou, D. Boroyevich, and R. Pindado, "New feedforward space-vector PWM method to obtain balanced AC output voltages in a three-level neutral-point-clamped converter", IEEE Trans. on Industrial Electronics, vol. 49, no. 5, pp. 1026-1034, Oct. 2002.
- B. Fuld, "Aufwandsarmer Thyristor-Dreistufen-Wechselrichter mit geringen Verlusten," in etzArchiv, vol. 11, pp. 261-264, VDE-Verlag, Berlin, Germany, 1989.
- L. Ma, T. Kerekes, R. Teodorescu, X. Jin, D. Florica, and M. Liserre, "The high efficiency transformer-less PV inverter topologies derived from NPC topology," in Proc. 13th European Conf. Power Electronics and Applications EPE '09, pp. 1-10, 2009.
- N. Celanovic and D. Boroyevich, "A comprehensive study of neutral-point voltage balancing problem in three-level neutral-point-clamped voltage source PWM inverters," IEEE Trans. Power Electron., vol. 15, pp. 242-249, March 2000.

Thank You !

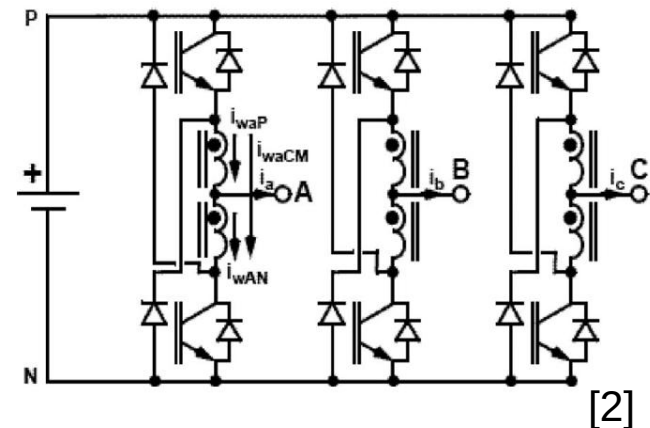


Alternative three-level concepts

Flying Capacitor 3-level converter



Coupled inductor 3-level converter



[1]: Fazel, S.S.; Bernet, S.; Krug, D.; Jalili, K.; , "Design and Comparison of 4-kV Neutral-Point-Clamped, Flying-Capacitor, and Series-Connected H-Bridge Multilevel Converters," *IEEE Transactions on Industry Applications*, , vol.43, no.4, pp.1032-1040, July-aug. 2007

[2]: Ewanchuk, J.; Salmon, J.; Knight, A.M.; , "Performance of a High-Speed Motor Drive System Using a Novel Multilevel Inverter Topology," *IEEE Transactions on Industry Applications*, , vol.45, no.5, pp.1706-1714, Sept.-oct. 2009